AMENDMENTS OF THE CLAIMS

The following listing of claims will replace all prior versions, and listings, of claims in the subject application:

LISTING OF CLAIMS

Claims 1 - 20 (canceled)

Claim 21 (currently amended): [[A]] <u>An initialized</u> rewritable phase-change optical recording medium comprising a substrate, a recording layer containing at least materials capable of carrying out read/write/erase operations through phase changes of said materials therein, and a metal/alloy layer,

wherein said recording layer consists essentially of Ag, In, Sb, Te and Ge, with a proportion in atomic percent of a(Ag): b(In): c(Sb): d(Te): e(Ge), with $0.1 \le a \le 7$, $2 \le b \le 10$, $64 \le c \le 92$, $5 \le d \le 26$ and $0.3 \le e \le 3$, provided that $a + b + c + d + e \ge 97$,

wherein said recording medium is initialized at least by irradiating said recording medium with a scanning beam spot emitted from a high power semiconductor laser device, wherein an energy density input by said beam spot is in a range of 600 J/m^2 to 1000 J/m^2 ,

wherein said recording medium is rewritable at a linear recording velocity ranging from 9 m/sec to 30 m/sec, and

wherein said metal/alloy layer includes Al and at least one kind of additive with a content ranging from 0.3 weight percent to 2.5 weight percent, said additive being selected from the group consisting of Ta, Ti, Cr and Si.

Claims 22 - 23 (canceled)

Claim 24 (currently amended): [[A]] <u>An initialized</u> rewritable phase-change optical recording medium as claimed in claim 21, wherein a scanning speed of said beam spot is in a range of 3.5 m/sec to 6.5 m/sec.

Claims 25 - 26 (canceled)

Claim 27 (currently amended): [[A]] An initialized rewritable phase-change optical recording medium as claimed in claim 21, wherein an intensity of the emission from said semiconductor laser device is equal to, or greater than, 330 mW.

Claims 28 - 29 (canceled)

Claim 30 (currently amended): [[A]] An initialized rewritable phase-change optical recording medium as claimed in claim 21, wherein a width of an overlapped portion, which is formed as an overlap of irradiated portions of two neighboring irradiation tracks on said recording medium during two consecutive rotations of said recording medium in initializing steps, is equal to, or less than, 0.5 Wr, where Wr is a width at half maximum of a spatial laser power distribution in a direction perpendicular to a beam scanning direction.

Claims 31 - 43 (canceled)

Claim 44 (previously presented): A phase-change optical recording medium comprising a substrate and a recording layer, wherein said recording layer stores information recorded in advance therein corresponding to:

data written as test recording runs with recording power, P, of laser beam consecutively varied in a range of 15 mW to 18 mW to thereby generate a recorded pattern including low and high reflective portions, and

S and R values for selecting an optimum recording power, said S and R values being specified by the following:

recorded signal amplitude, m, obtained from read out signals from said low and high reflective portions on said recording medium corresponding to said recording power, P;

a normalized gradient, g(P), calculated from an equation,

 $g(P) = (m/\Delta m)/(P/\Delta P)$,

where ΔP is an infinitesimal change in the vicinity of P, and Δm is an

infinitesimal change in the vicinity of m;

an optimum recording power, determined after judging adequacy of the magnitude of said recording power, P, based on thus calculated normalized gradient, g(P), wherein:

S, is a specific number selected from the numbers in the range of 0.2 to 2.0 based on said calculated normalized gradient, g(P);

Ps is a value of said recording power which coincides with said selected specific number, S;

R is a specific number, based on the obtained recording power, Ps selected from the numbers in the range of 1.0 to 1.7, and

wherein said recording power, P_s , is multiplied by said specific number, R, to obtain an optimum recording power value, P_0 .

Claim 45 (original): The phase-change optical recording medium according to claim 44, wherein $1.2 \le S \le 1.4$, and $1.1 \le R \le 1.3$.

Claim 46 (original): The phase-change optical recording medium according to claim 44, wherein said recording medium is recordable at a recording velocity ranging from 4.8 m/sec to 14.0 m/sec.

Claim 47 (currently amended): A phase-change optical recording medium comprising a substrate and a recording layer, wherein said recording layer stores information recorded in advance therein corresponding to:

data written as test recording runs with recording power, P, of laser beam consecutively varied in a range of 15 mW to 18 mW to thereby generate a recorded pattern including low and high reflective portions, and

a [[P_1]] \underline{P}_t value corresponding to an optimum recording power, P_0 , specified by the following:

recorded signal amplitude, m, obtained from read out signals from said low and high reflective portions on said recording medium corresponding to said recording power, P;

a normalized gradient, g(P), calculated from an equation,

 $g(P)=(m/\Delta m)/(P/\Delta P)$,

where ΔP is an infinitesimal change in the vicinity of P, and Δm is an infinitesimal change in the vicinity of m;

an optimum recording power, determined after judging adequacy of the magnitude of said recording power, P, based on thus calculated normalized gradient, g(P), wherein:

S is a specific number selected from the numbers in the range of 0.2 to 2.0 based on said calculated normalized gradient, g(P);

Ps is a value of said recording power which coincides with said selected specific number, S;

wherein R is a specific number, based on the obtained recording power, Ps, from the numbers in the range of 1.0 to 1.7;

wherein said recording power, Ps, is multiplied by said specific number, R, to obtain said P_t value corresponding to said optimum recording power, P_0 .

Claim 48 (original): The phase-change optical recording medium according to claim 47, wherein said recording medium is recordable at a recording velocity ranging from 4.8 m/sec to 14.0 m/sec.

Claim 49 (currently amended): [[A]] An initialized rewritable phase-change optical recording medium as claimed in claim 21, wherein a 3T land jitter of the initialized optical recording medium after 1000 cycles of direct overwrite is equal to or below 35 nsec.

Claim 50 (currently amended): [[A]] An initialized rewritable phase-change optical recording medium as claimed in claim 21, wherein a 3T land jitter of the initialized optical recording medium is equal to or below 35 nsec.

Claim 51 (currently amended): An optical recording medium comprising a substrate, a recording layer containing at least materials capable of carrying out read/write/erase operations through phase changes of said materials therein, and a metal/alloy layer,

wherein said recording layer consists essentially of Ag, In, Sb, Te and Ge, with a proportion in atomic percent of a(Ag): b(In): c(Sb): d(Te): e(Ge), with $0.1 \le a \le 7$, $2 \le b \le 10$, $64 \le c \le 92$, $5 \le d \le 26$ and $0.3 \le e \le 3$, provided that $a + b + c + d + e \ge 97$,

wherein said recording medium is rewritable at a linear recording velocity ranging from 9 m/sec to 30 m/sec, and has a capability of at least 3000 overwrite cycles, and

wherein said metal/alloy layer includes Al and at least one kind of additive with a content ranging from 0.3 weight percent to 2.5 weight percent, said additive being selected from the group consisting of Ta, Ti, Cr and Si.

Claim 52 (previously presented): The optical recording medium according to claim 51, wherein said recording layer has a composition satisfying a relation of $88 \le c + d \le 98$.

Claim 53 (previously presented): The optical recording medium of claim 51, further comprising contiguous layers formed on said substrate in order as follows, a first dielectric layer, the recording layer, a second dielectric layer, the metal/alloy layer, and an ultraviolet light curing resinous layer.

Claim 54 (previously presented): The optical recording medium according to claim 53, wherein said first dielectric layer, recording layer, second dielectric layer and metal/alloy layer are each formed having a thickness ranging from 30 nm to 220 nm, 10 nm to 25 nm, 10 nm to 50 nm, and 70 nm to 250 nm, respectively.

Claims 55 - 57 (canceled)

Claim 58 (currently amended): An optical recording medium comprising a substrate, a recording layer containing at least materials capable of carrying out read/write/erase operations through phase changes of said materials therein, and a metal/alloy layer,

wherein said recording layer consists essentially of Ag, In, Sb, Te and Ge, with a proportion in atomic percent of a(Ag): b(In): c(Sb): d(Te): e(Ge), with $0.1 \le a \le 7$, $2 \le b \le 10$, $64 \le c \le 92$, $5 \le d \le 26$ and $0.3 \le e \le 3$, provided that $a + b + c + d + e \ge 97$,

wherein said recording medium is rewritable at a linear recording velocity ranging from 9 m/sec to 30 m/sec, and has a capability of at least 3000 overwrite cycles, and

wherein said metal/alloy layer includes Ag and at least one kind of additive with a content ranging from 0 to 4 weight percent, said additive being selected from the group consisting of Au, Pt, Pd, Ru, Ti and Cu.

Claim 59 (previously presented): The optical recording medium according to claim 58, wherein said recording layer has a composition satisfying a relation of $88 \le c + d \le 98$.

Claim 60 (previously presented): The optical recording medium of claim 58, further comprising contiguous layers formed on said substrate in order as follows, a first dielectric layer, the recording layer, a second dielectric layer, the metal/alloy layer, and an ultraviolet light curing resinous layer.

Claim 61 (previously presented): The optical recording medium according to claim 60, wherein said first dielectric layer, recording layer, second dielectric layer and metal/alloy layer are each formed having a thickness ranging from 30 nm to 220 nm, 10 nm to 25 nm, 10 nm to 50 nm, and 70 nm to 250 nm, respectively.

Claim 62 (canceled)

Claim 63 (currently amended): [[A]] <u>An initialized</u> rewritable phase-change optical recording medium comprising a substrate, a recording layer containing at least materials capable of carrying out read/write/erase operations through phase changes of said materials therein, and a metal/alloy layer,

wherein said recording layer consists essentially of Ag, In, Sb, Te and Ge, with a proportion in atomic percent of a(Ag): b(In): c(Sb): d(Te): e(Ge), with $0.1 \le a \le 7$, $2 \le b \le 10$, 64 $\le c \le 92$, $5 \le d \le 26$ and $0.3 \le e \le 3$, provided that $a + b + c + d + e \ge 97$,

wherein said recording medium is initialized at least by irradiating said recording medium with a scanning beam spot emitted from a high power semiconductor laser device, wherein an energy density input by said beam spot is in a range of 600 J/m² to 1000 J/m², and

wherein said metal/alloy layer includes Ag and at least one kind of additive with a content ranging from 0 to 4 weight percent, said additive being selected from the group consisting of Au, Pt, Pd, Ru, Ti and Cu.

Claim 64 (currently amended): [[A]] <u>An initialized</u> rewritable phase-change optical recording medium as claimed in claim 63, wherein a scanning speed of said beam spot is in a range of 3.5 m/sec to 6.5 m/sec.

Claim 65 (currently amended): [[A]] <u>An initialized</u> rewritable phase-change optical recording medium <u>method</u> as claimed in claim 63, wherein an intensity of the emission from said semiconductor laser device is equal to, or greater than, 330 mW.

Claim 66 (currently amended): [[A]] An initialized rewritable phase-change optical recording medium as claimed in claim 63, wherein a width of an overlapped portion, which is formed as an overlap of irradiated portions of two neighboring irradiation tracks on said recording medium during two consecutive rotations of said recording medium in initializing steps, is equal to, or less than, 0.5 Wr, where Wr is a width at half maximum of a spatial laser power distribution in a direction perpendicular to a beam scanning direction.